

PDTB113/123/143/114EQA series

50 V, 500 mA PNP resistor-equipped transistors

Rev. 1 — 30 March 2016

Product data sheet

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistor (RET) family in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

Table 1. Product overview

Type number	R1	R2	Package Nexperia	NPN complement
PDTB113EQA	1 kΩ	1 kΩ	DFN1010D-3	PDTD113EQA
PDTB123EQA	2.2 kΩ	2.2 kΩ	(SOT1215)	PDTD123EQA
PDTB143EQA	4.7 kΩ	4.7 kΩ		PDTD143EQA
PDTB114EQA	10 kΩ	10 kΩ		PDTD114EQA

1.2 Features and benefits

- 500 mA output current capability
- Built-in bias resistors
- ± 10% resistor ratio tolerance
- Simplifies circuit design
- Reduces component count
- Reduced pick and place costs
- Low package height of 0.37 mm
- Suitable for Automatic Optical Inspection (AOI) of solder joint
- AEC-Q101 qualified

1.3 Applications

- Digital applications
- Cost saving alternative for BC807/BC817 series in digital applications
- Controlling IC inputs
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
lo	output current		-	-	-500	mΑ



2. Pinning information

Table 3. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	GND	GND (emitter)		
3	0	output (collector)		I R1
4	0	output (collector)	2 4 3 Transparent top view	GND

3. Ordering information

Table 4. Ordering information

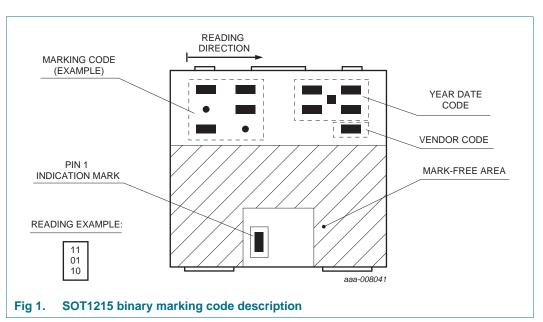
Type number	Package					
	Name	Description	Version			
PDTB113EQA	DFN1010D-3	plastic thermal enhanced ultra thin small outline	SOT1215			
PDTB123EQA		package; no leads; 3 terminals; body: 1.1 × 1.0 × 0.37 mm				
PDTB143EQA						
PDTB114EQA						

4. Marking

Table 5. Marking codes

Type number	Marking code
PDTB113EQA	00 00 01
PDTB123EQA	01 01 01
PDTB143EQA	01 01 11
PDTB114EQA	01 10 11

4.1 Binary marking code description



5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

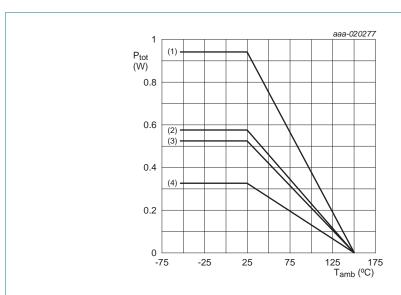
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V _{EBO}	emitter-base voltage	open collector	-	-10	V

Table 6. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Min	Max	Unit						
VI	input voltage	input voltage								
	PDTB113EQA		-10	+10	V					
	PDTB123EQA		-12	+10	V					
	PDTB143EQA		-30	+10	V					
	PDTB114EQA		-50	+10	V					
Io	output current		-	-500	mA					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] _	325	mW					
			[2] _	575	mW					
			[3] _	525	mW					
			[4] _	940	mW					
Tj	junction temperature		-	150	°C					
T _{amb}	ambient temperature		-55	+150	°C					
T _{stg}	storage temperature		-65	+150	°C					

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm².



- (1) FR4 PCB, 4-layer copper, 1 cm²
- (2) FR4 PCB, single-sided copper, 1 cm²
- (3) FR4 PCB, 4-layer copper, standard footprint
- (4) FR4 PCB, single sided copper, standard footprint

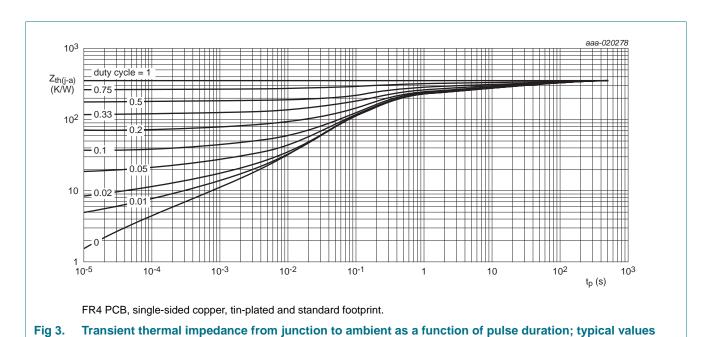
Fig 2. Power derating curves

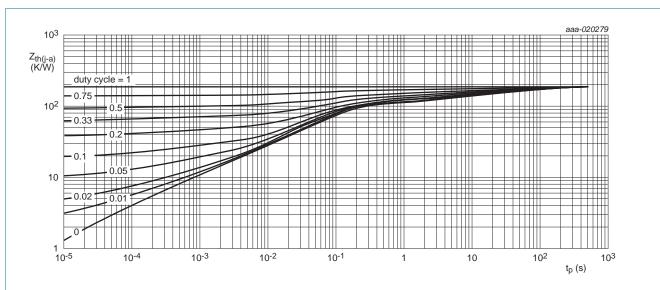
6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Parameter Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction	in free air	<u>[1]</u>	-	-	385	K/W
to ambient		[2]	-	-	218	K/W	
			[3]	-	-	239	K/W
			<u>[4]</u>	-	-	133	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	40	K/W

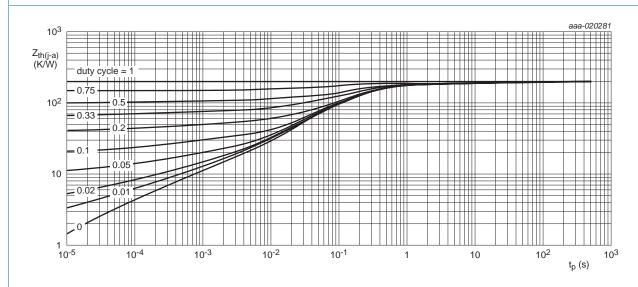
- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated; mounting pad for collector 1 cm².





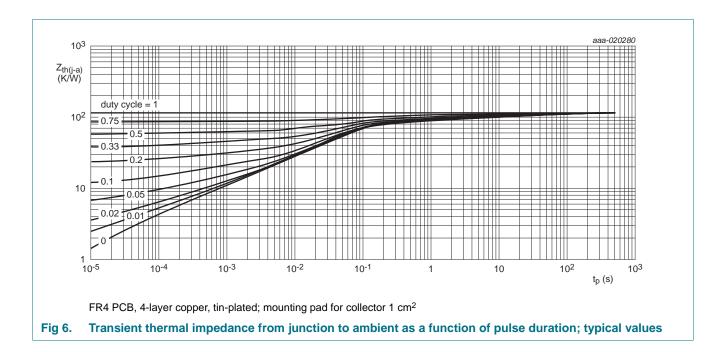
FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, tin-plated and standard footprint.

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



7. Characteristics

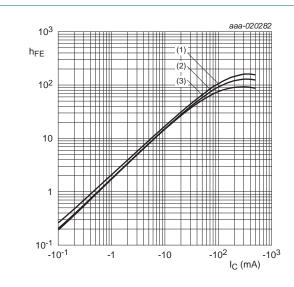
Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -50 \text{ V}; I_B = 0 \text{ A}$	-	-	-0.5	μА
I _{EBO}	emitter-base cut-off curr	ent		,		
	PDTB113EQA	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-4	mA
	PDTB123EQA		-	-	-2	mA
	PDTB143EQA		-	-	-0.9	mA
	PDTB114EQA		-	-	-0.4	mA
h _{FE}	DC current gain					
	PDTB113EQA	$V_{CE} = -5 \text{ V}; I_{C} = -50 \text{ mA}$	33	-	-	
	PDTB123EQA		40	-	-	
	PDTB143EQA		60	-	-	
	PDTB114EQA		70	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -50 \text{ mA}$; $I_B = -2.5 \text{ mA}$	-	-	-100	mV
V _{I(off)}	off-state input voltage					
PDTB113EQA	PDTB113EQA	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-0.6	-1.05	-1.5	V
	PDTB123EQA		-0.6	-1.05	-1.8	V
	PDTB143EQA		-0.6	-1.05	-1.5	V
	PDTB114EQA		-0.6	-1.05	-1.5	V
V _{I(on)}	on-state input voltage					
	PDTB113EQA	$V_{CE} = -0.3 \text{ V; } I_{C} = -20 \text{ mA}$	-1	-1.45	-1.8	V
	PDTB123EQA		-1	-1.5	-2	V
	PDTB143EQA		-1	-1.7	-2.2	V
	PDTB114EQA		-1	-2.2	-3	V
R1	bias resistor 1 (input)	[1]				
	PDTB113EQA		0.7	1	1.3	kΩ
	PDTB123EQA		1.54	2.2	2.86	kΩ
	PDTB143EQA		3.3	4.7	6.1	kΩ
	PDTB114EQA		7	10	13	kΩ
R2/R1	bias resistor ratio	[1]	0.9	1	1.1	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$	-	7	-	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V; } I_{C} = -50 \text{ mA; } f = 100 \text{ MHz}$	-	150	-	MHz

^[1] See section test information for resistor calculation and test conditions.

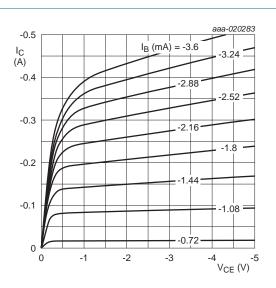
^[2] Characteristics of built-in transistor.



$$V_{CE} = -5 \text{ V}$$

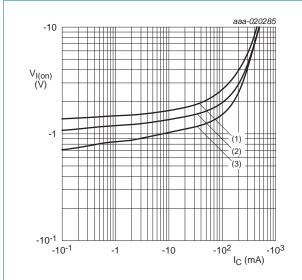
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 7. PDTB113EQA: DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

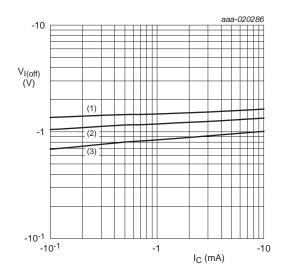
Fig 8. PDTB113EQA: Collector current as a function of collector-emitter voltage; typical values





- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) T_{amb} = 100 °C

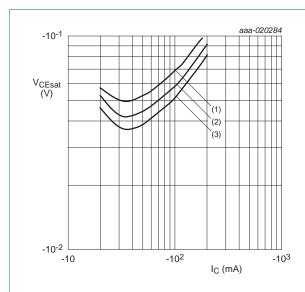
Fig 9. PDTB113EQA: On-state input voltage as a function of collector current; typical values



 $V_{CE} = -5 \text{ V}$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

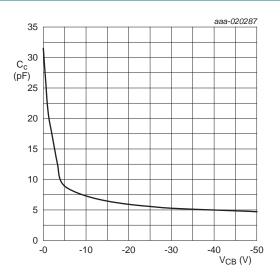
Fig 10. PDTB113EQA: Off-state input voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

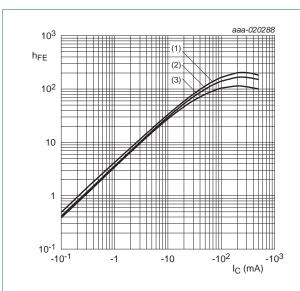
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 11. PDTB113EQA: Collector-emitter saturation voltage as a function of collector current; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig 12. PDTB113EQA: Collector capacitance as a function of collector-base voltage; typical values



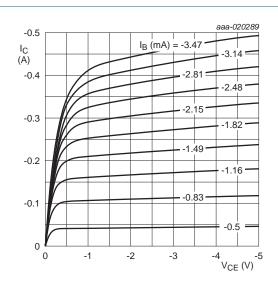
 $V_{CE} = -5 \text{ V}$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

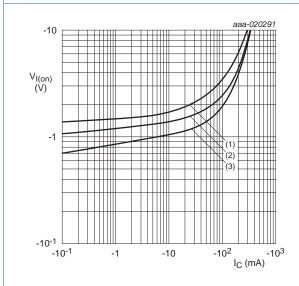
(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 13. PDTB123EQA: DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig 14. PDTB123EQA: Collector current as a function of collector-emitter voltage; typical values



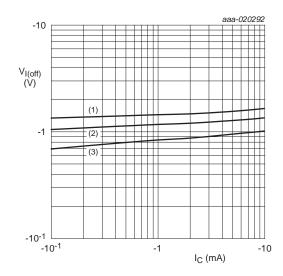
 $V_{CE} = -0.3 \text{ V}$

(1) $T_{amb} = -40 \, ^{\circ}C$

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 15. PDTB123EQA: On-state input voltage as a function of collector current; typical values



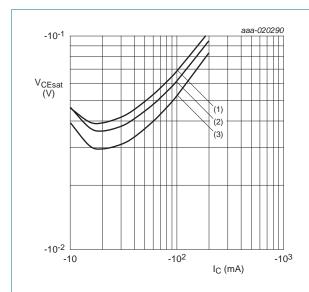
 $V_{CE} = -5 \text{ V}$

(1) $T_{amb} = -40 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

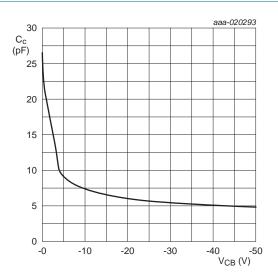
Fig 16. PDTB123EQA: Off-state input voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

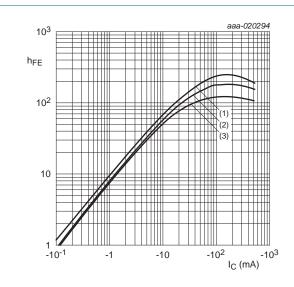
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 17. PDTB123EQA: Collector-emitter saturation voltage as a function of collector current; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

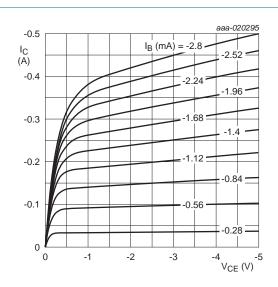
Fig 18. PDTB123EQA: Collector capacitance as a function of collector-base voltage; typical values





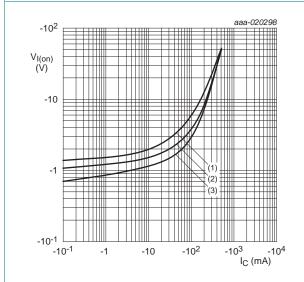
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 19. PDTB143EQA: DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

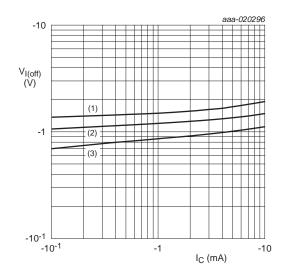
Fig 20. PDTB143EQA: Collector current as a function of collector-emitter voltage; typical values





- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) T_{amb} = 100 °C

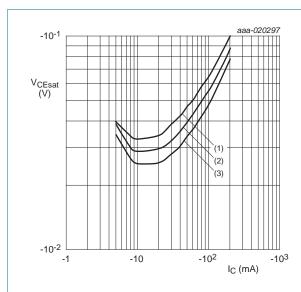
Fig 21. PDTB143EQA: On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

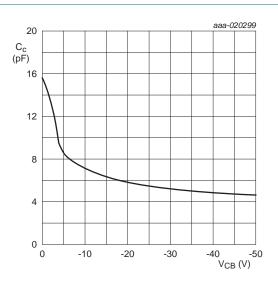
Fig 22. PDTB143EQA: Off-state input voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

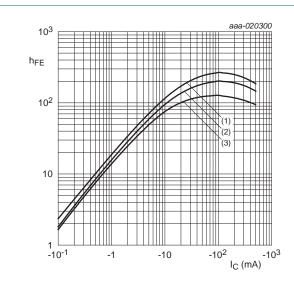
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 23. PDTB143EQA: Collector-emitter saturation voltage as a function of collector current; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

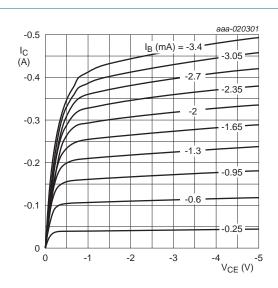
Fig 24. PDTB143EQA: Collector capacitance as a function of collector-base voltage; typical values



$$V_{CE} = -5 \text{ V}$$

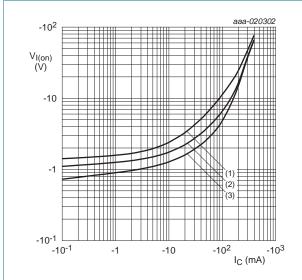
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 25. PDTB114EQA: DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

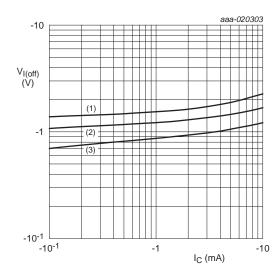
Fig 26. PDTB114EQA: Collector current as a function of collector-emitter voltage; typical values





- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) T_{amb} = 100 °C

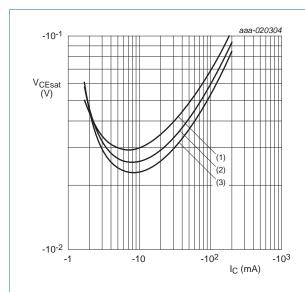
Fig 27. PDTB114EQA: On-state input voltage as a function of collector current; typical values



 $V_{CE} = -5 \text{ V}$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

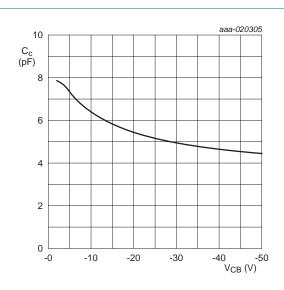
Fig 28. PDTB114EQA: Off-state input voltage as a function of collector current; typical values



 $I_C/I_B = 20$

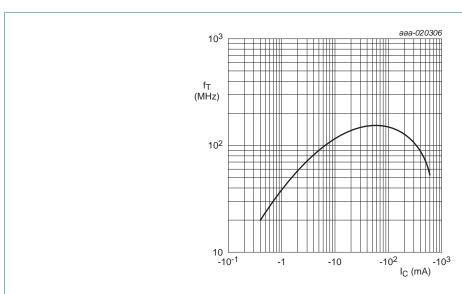
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 29. PDTB114EQA: Collector-emitter saturation voltage as a function of collector current; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig 30. PDTB114EQA: Collector capacitance as a function of collector-base voltage; typical values



 $V_{CE} = -5 \text{ V; } f = 100 \text{ MHz; } T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig 31. Transition frequency as a function of collector current; typical values of built-in transistor

PDTB113_123_143_114EQA_SER

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

8.2 Resistor calculation

• Calculation of bias resistor 1 (R1):

$$R1 = \frac{V(I_{I2}) - V(I_{I1})}{I_{I2} - I_{I1}}$$

• Calculation method A of bias resistor ratio (R2/R1):

$$\frac{R2}{R1} = \frac{V(I_{I3})}{R1 \cdot I_{I3}} - 1$$

• Calculation method B of bias resistor ratio (R2/R1):

$$\frac{R2}{RI} = \frac{V(I_{I4}) - V(I_{I3})}{RI \cdot (I_{I4} - I_{I3})} - 1$$

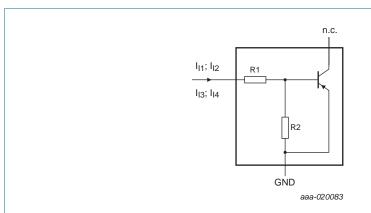


Fig 32. Resistor test circuit

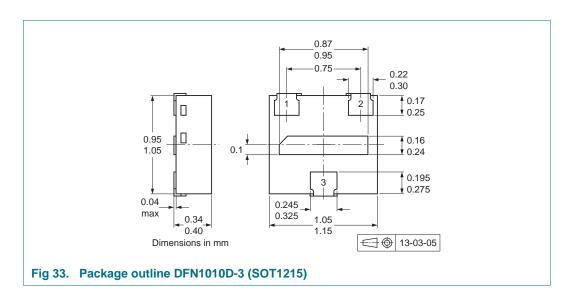
8.3 Resistor test conditions

Table 9. Resistor test conditions

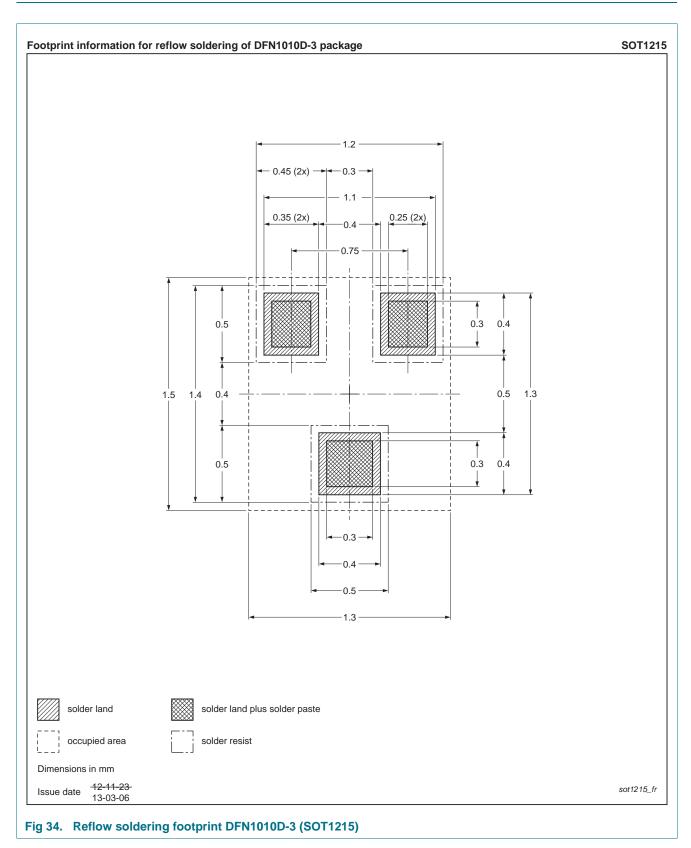
Type number		R1	R2	Test conditions			
		kΩ	kΩ	I _{I1}	I _{I2}	I _{I3}	I _{I4}
PDTB113EQA	[1]	1	1	–1.5 mA	–1.9 mA	2.20 mA	-
PDTB123EQA	[1]	2.2	2.2	–0.7 mA	–0.8 mA	0.75 mA	-
PDTB143EQA	[2]	4.7	4.7	–1.3 mA	–1.5 mA	1.05 mA	1.25 mA
PDTB114EQA	[2]	10	10	–0.7 mA	–0.8 mA	0.45 mA	0.55 mA

- [1] Uses calculation method A of bias resistor ratio R2/R1
- [2] Uses calculation method B of bias resistor ratio R2/R1

9. Package outline



10. Soldering



PDTB113_123_143_114EQA_SER

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTB113_123_143_114EQA_SER v.1	20160330	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

12.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

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PDTB113/123/143/114EQA

50 V, 500 mA PNP resistor-equipped transistors

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For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to:

salesaddresses@nexperia.com

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